

## IGBT MODULE ( L series)

### ■ Features

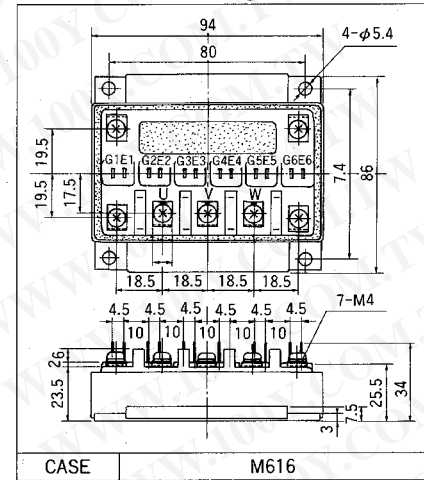
- High Speed Switching
- Low Saturation Voltage
- Voltage Drive

### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

**勝特力材料 886-3-5753170**  
**勝特力电子(上海) 86-21-34970699**  
**勝特力电子(深圳) 86-755-83298787**  
[Http://www.100y.com.tw](http://www.100y.com.tw)

### ■ Outline Drawings



### ■ Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings

Items	Symbols	Ratings	Units	
Collector-Emitter Voltage	V <sub>CEs</sub>	600	V	
Gate-Emitter Voltage	V <sub>GES</sub>	±20	V	
Collector Current	Continuous	I <sub>c</sub>	50	
	1ms	I <sub>c pulse</sub>	100	
	Continuous	-I <sub>c</sub>	50	
	1ms	-I <sub>c pulse</sub>	100	
Max. Power Dissipation	P <sub>c</sub>	250	W	
Operating Temperature	T <sub>j</sub>	+150	°C	
Storage Temperature	T <sub>stg</sub>	-40 to +125	°C	
Net. Weight		510	g	
Isolation Voltage	AC, 1min.	V <sub>isol</sub>	2500	V
			Mounting *1	35
Screw Torque			17	kg*cm
	Terminals *2			

\*1 Recommendable Value 25 to 35kg\*cm (M5)  
 \*2 Recommendable Value 13 to 17kg\*cm (M4)

#### ● Electrical Characteristics (T<sub>j</sub>=25°C)

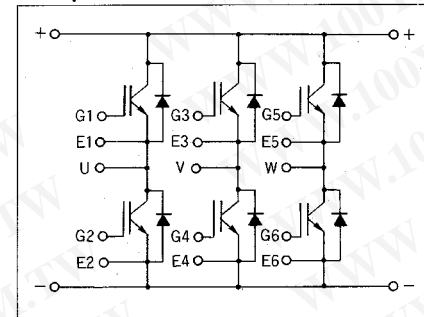
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I <sub>CEs</sub>	V <sub>GE</sub> =0V V <sub>CE</sub> =600V T <sub>j</sub> =25°C			1.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V V <sub>GE</sub> =±20V			100	nA
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> =20V I <sub>c</sub> =50mA	3.0		6.0	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V I <sub>c</sub> =50A		2.7	3.5	V
Input Capacitance	C <sub>ies</sub>	V <sub>GE</sub> =0V		4750		pF
Output Capacitance	C <sub>oes</sub>	V <sub>CE</sub> =10V		-		
Reverse Transfer Capacitance	C <sub>res</sub>	f=1MHz		-		
Turn-on Time *3	t <sub>on</sub>	V <sub>CC</sub> =300V		0.4	0.8	μs
	t <sub>r</sub>	I <sub>c</sub> =50A		0.3	0.6	
Turn-off Time *4	t <sub>off</sub>	V <sub>GE</sub> =±15V		0.6	1.0	μs
	t <sub>f</sub>	R <sub>G</sub> =51Ω		0.2	0.35	
Diode Forward On-Voltage	V <sub>F</sub>	I <sub>F</sub> =50A V <sub>GE</sub> =0V			2.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =50A -di/dt=150A/μs V <sub>GE</sub> =-10V			300	ns

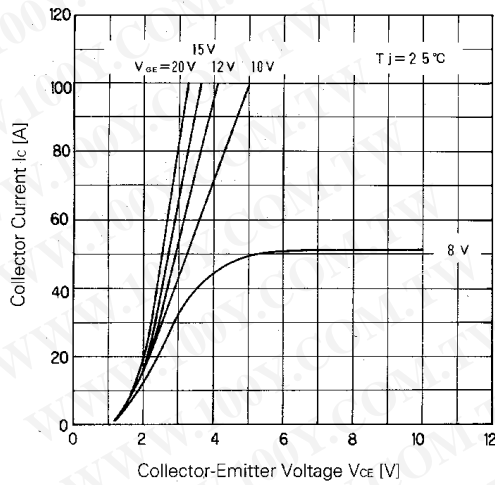
\*3 Resistive load      \*4 Inductive load

#### ● Thermal Characteristics

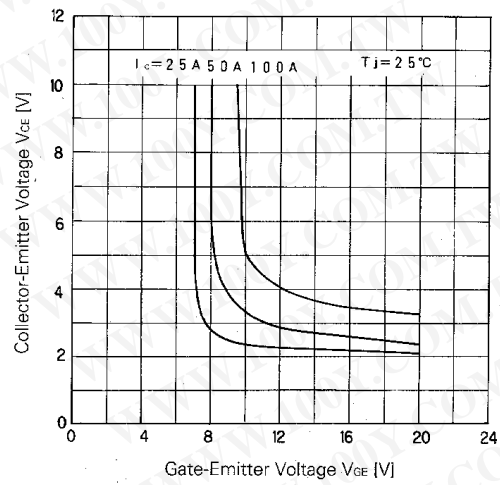
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R <sub>th(j-c)</sub>	IGBT			0.5	°C/W
	R <sub>th(j-e)</sub>	Diode			1.0	
	R <sub>th(c-f)</sub>	With Thermal compound		0.05		

### ■ Equilavelent Circuit Schematic

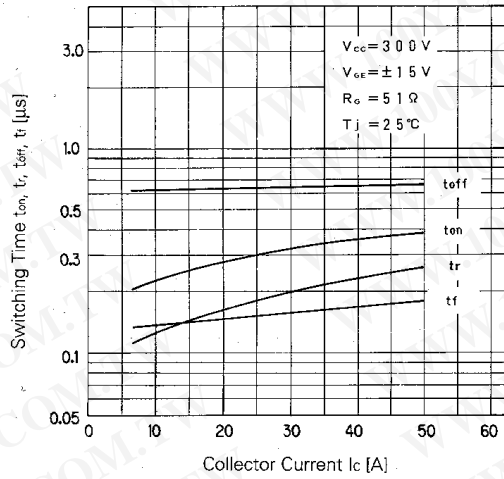




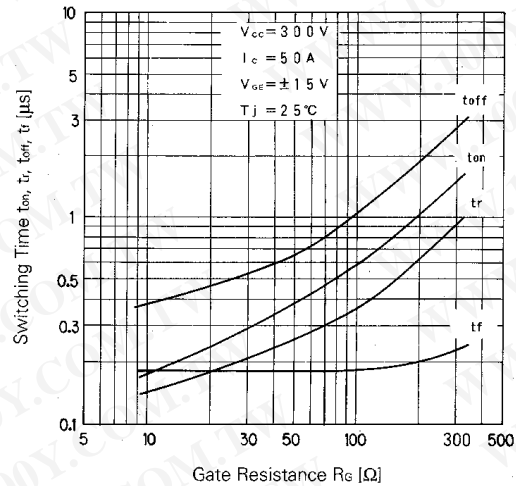
Collector Current vs. Collector-Emitter Voltage



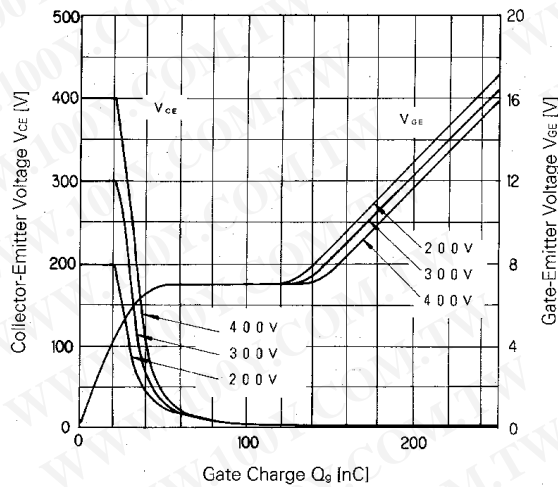
Collector-Emitter Voltage vs. Gate-Emitter Voltage



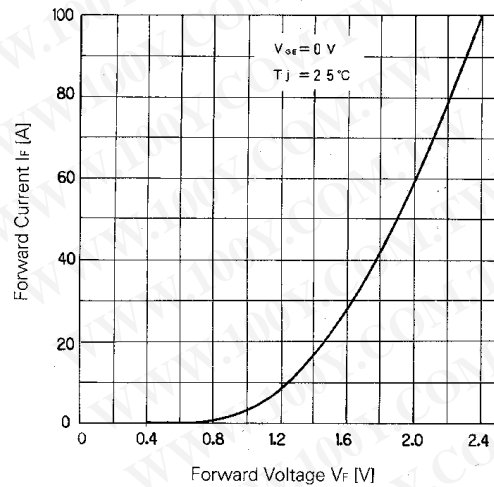
Switching Time



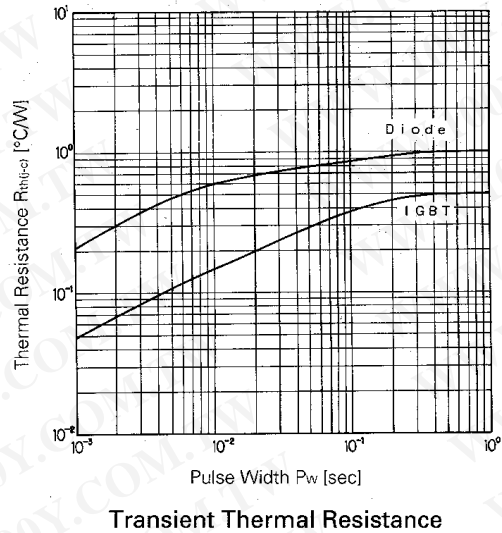
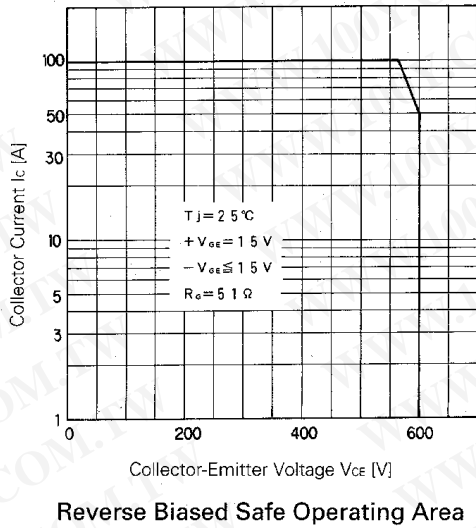
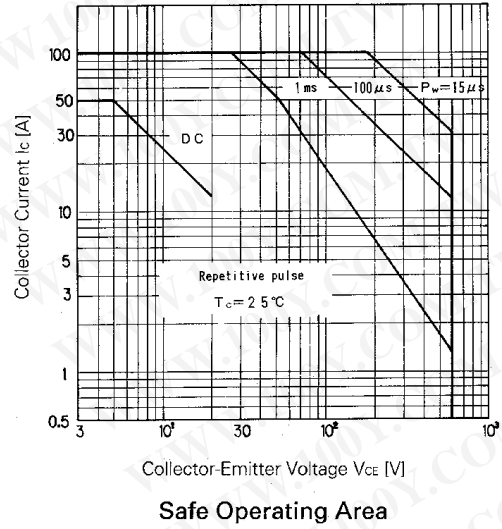
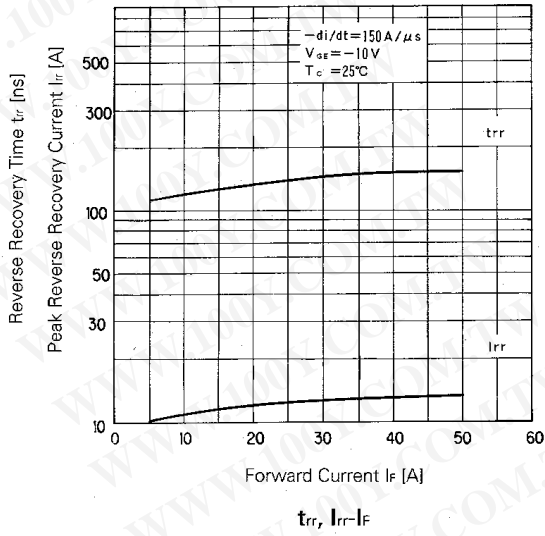
Switching Time-Gate Resistance



Dynamic Input Characteristic



Forward Voltage of Free Wheel Diode



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